One Watt Amplifier Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector - Emitter Voltage	MPSW05 MPSW06	V _{CEO}	60 80	Vdc
Collector - Base Voltage	MPSW05 MPSW06	V _{CBO}	60 80	Vdc
Emitter - Base Voltage		V _{EBO}	4.0	Vdc
Collector Current – Continuous		I _C	500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C		P _D	1.0 8.0	W mW/°C
Total Device Dissipation @ T _C Derate above 25°C	= 25°C	P_D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	n	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

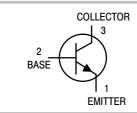
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	50	°C/W

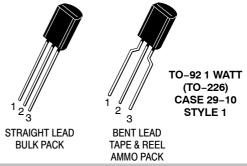
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



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MARKING DIAGRAM



= 5 or 6

A = Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSW05G	TO-92 (Pb-Free)	5000 Units/Bulk
MPSW06G	TO-92 (Pb-Free)	5000 Units/Bulk
MPSW06RLRA	TO-92	2000/Tape & Reel
MPSW06RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•		•
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	MPSW05 MPSW06	V _{(BR)CEO}	60 80	_ _	Vdc
Emitter – Base Breakdown Voltage $(I_E = 100 \mu Adc, I_C = 0)$		V _{(BR)EBO}	4.0	_	Vdc
Collector Cutoff Current $(V_{CE} = 40 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$	MPSW05 MPSW06	I _{CES}	- -	0.5 0.5	μAdc
Collector Cutoff Current $(V_{CB} = 40 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$	MPSW05 MPSW06	I _{CBO}	- -	0.1 0.1	μAdc
Emitter Cutoff Current (V _{EB} = 3.0 Vdc, I _C = 0)		I _{EBO}	_	0.1	μAdc
ON CHARACTERISTICS (Note 1)					
DC Current Gain ($I_C = 50 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 250 \text{ mAdc}$, $V_{CE} = 1.0 \text{ Vdc}$)		h _{FE}	80 60	_ _	-
Collector – Emitter Saturation Voltage (I _C = 250 mAdc, I _B = 10 mAdc)		V _{CE(sat)}	-	0.4	Vdc
Base-Emitter Saturation Voltage (I _C = 250 mAdc, V _{CE} = 5.0 Vdc)		V _{BE(sat)}	-	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 200 mAdc, V _{CE} = 5.0 Vdc, f = 20 MHz)		f _T	50	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)		C _{obo}	-	12	pF

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

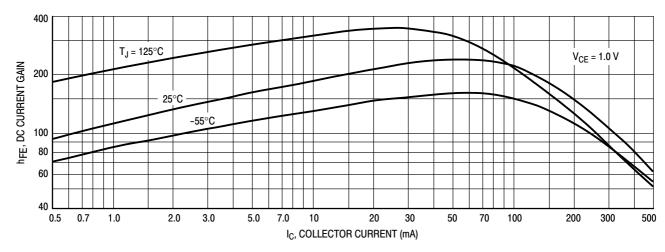


Figure 1. DC Current Gain

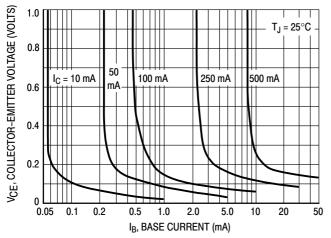


Figure 2. Collector Saturation Region

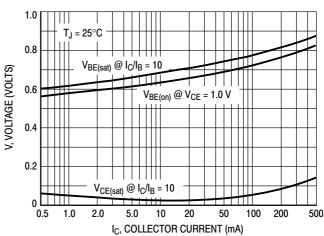


Figure 3. "On" Voltages

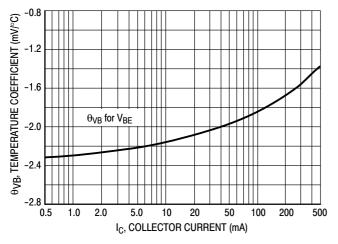


Figure 4. Base-Emitter Temperature Coefficient

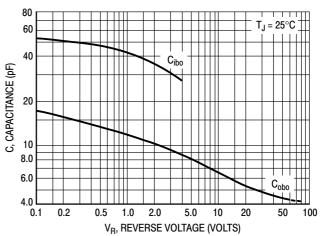


Figure 5. Capacitance

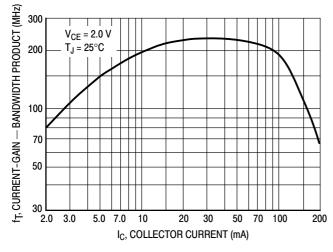


Figure 6. Current-Gain - Bandwidth Product

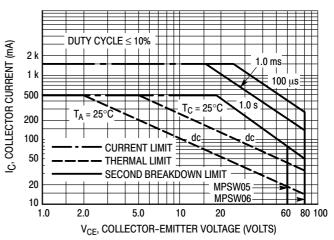
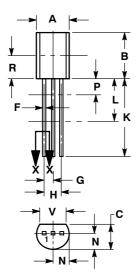


Figure 7. Active Region - Safe Operating Area

PACKAGE DIMENSIONS

TO-92 (TO-226) 1 WATT CASE 29-10 **ISSUE O**



STRAIGHT LEAD **BULK PACK**



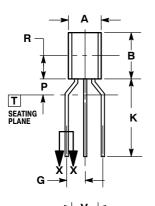
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1994.
 CONTROLLING DIMENSION: INCHES.
- CONTINUE DIMENSION: INCHES.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DI-MENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250	-	6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.135		3.43	
٧	0.135		3.43	

STYLE 1: PIN 1. EMITTER

BASE COLLECTOR



BENT LEAD TAPE & REEL AMMO PACK



NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN
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В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.135		3.43	
V	0.135		3.43	

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